

# IRPS 2015

## IEEE International Reliability Physics Symposium

### Sunday Tutorial Presentations

April 19, 2015

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- S1.1: FEOL Reliability Hot Carrier Effects in MOSFET Device
- S1.2: Process Integration and Variability Interaction with BEOL Reliability
- S1.3: Middle of Line (MOL) Reliability - in between FEOL and BEOL
- S1.4: A New Era of Close Interaction of Different Reliability Mechanisms
- S2.1: Aging Simulation of Circuit: Models and Applications
- S2.2: Circuit Aging Tools Reliability Verification
- S2.3: Analysis of Chip Level Soft Error Effects
- S2.4: Advanced NVM Part I – MRAM
- S3.1: System Level Stress
- S3.2: Designing in Reliability of Complex Electronic Devices: System level Impact of Multi-physics Interactions
- S3.3: System Level Electrical Overstress (EOS) and ESD - Part I
- S3.3: System Level Electrical Overstress (EOS) and ESD - Part II
- S3.3: System Level Electrical Overstress (EOS) and ESD - Part III
- S3.3: System Level Electrical Overstress (EOS) and ESD - Part IV
- S3.3: System Level Electrical Overstress (EOS) and ESD - Part V
- S3.4: Radiation Effects at the System Level

